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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Inventor: Tatau NISHINAGA

Group Art Unit: 1765

Appln. No.: 09/511,912

Examiner: M. Anderson

Filed: February 23, 2000

For: A METHOD FOR FORMING A SINGLE CRYSTALLINE FILM

#21/29  
Mda  
12/27/02

SUPPLEMENTAL AMENDMENT UNDER 37 CFR § 1.111

Assistant Commissioner of Patents  
Washington, D.C. 20231

Sir:

Supplemental to the Amendment filed December 12, 2002, the Applicant requests further amendment of the above-captioned application as follows:

IN THE CLAIMS:

Kindly add the following new claims.

--20. The method of claim 1, wherein:

the single crystalline substrate is formed from one of the group of Si, GaAs, ZnSe, SrTiO<sub>3</sub>, and sapphire; and

the single crystalline film is formed from one of the group of Si, GaAs, Ga<sub>1-x</sub>Al<sub>x</sub>As, ZnSe, ZnS, CdTe, ZnS<sub>1-x</sub>Se<sub>x</sub>, and YBCO.

21. The method of claim 1, wherein:

the single crystalline substrate is formed from one of the group of Si, GaAs, ZnSe, and SrTiO<sub>3</sub>; and